Silicon PNP Power Transistors 2SA907/908/909

DESCRIPTION

·With TO-3 package
·Complement to type 2SC1584/1585/1586

APPLICATIONS

·For power switching and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA907	Open emitter	-100	V
		2SA908		-150	
		2SA909		-200	
V_{CEO}	Collector-emitter voltage	2SA907	Open base	-100	V
		2SA908		-150	
		2SA909		-200	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-15	A
I_B	Base current			-5	A
P_C	Collector power dissipation		T_C=25□	150	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-65~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA907	I_C=-50mA ;I_B=0	-100			V
		2SA908		-150			
		2SA909		-200			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-10A; I_B=-1A			-3.0	V
I_{CBO}	Collector cut-off current	2SA907	V_{CB}=-100V; I_E=0			-1.0	mA
		2SA908	V_{CB}=-150V; I_E=0				
		2SA909	V_{CB}=-200V; I_E=0				
I_{EBO}	Emitter cut-off current		V_{EB}=-6V; I_C=0			-1.0	mA
h_{FE}	DC current gain		I_C=-5A ; V_{CE}=-4V	30			
f_T	Transition frequency		I_C=-0.5A ; V_{CE}=-12V		10		MHz

PACKAGE OUTLINE

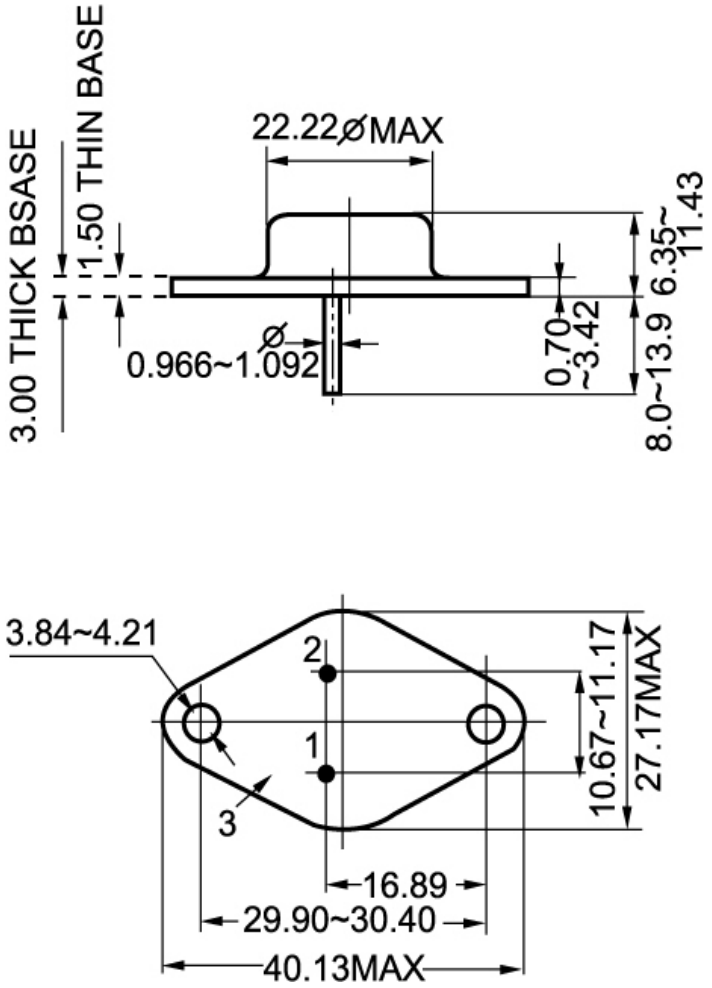

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)